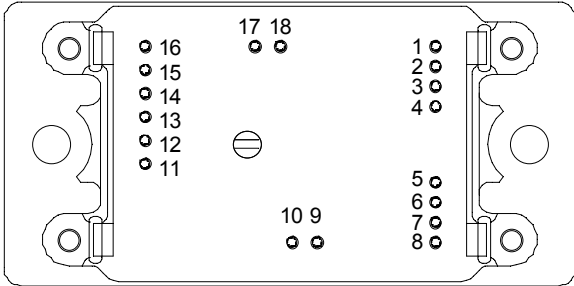
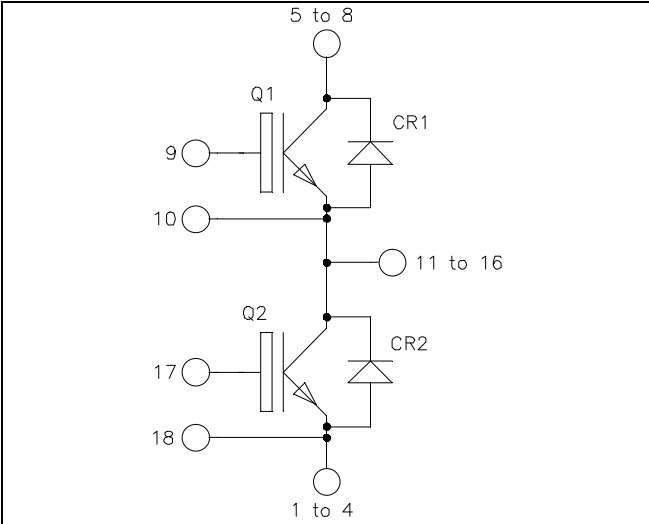


Phase leg
NPT IGBT Power Module

$V_{CES} = 1200V$
 $I_C = 100A @ T_c = 80^\circ C$



Pins 1/2/3/4 ; 5/6/7/8 ; 11/12/13/14/15/16 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) Fast IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_c of V_{CEsat}
- RoHS Compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	135
		$T_c = 80^\circ C$	100
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	300
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	568
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	200A @ 1200V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Electrical Characteristics

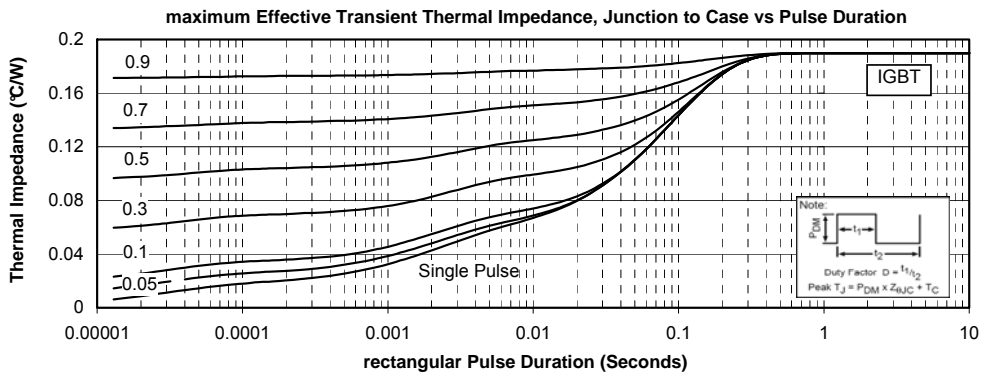
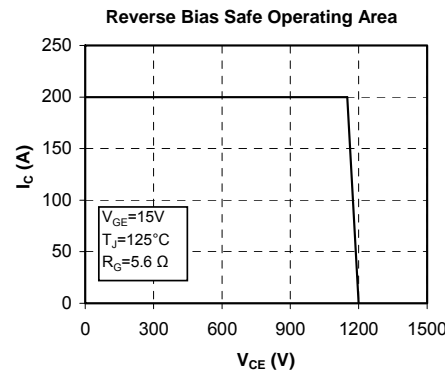
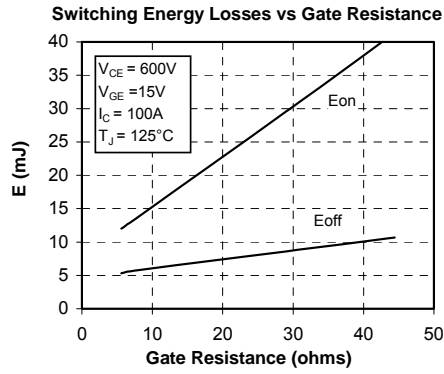
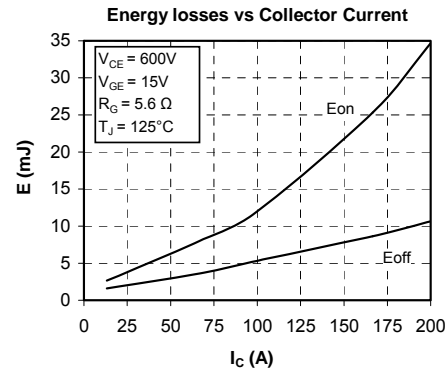
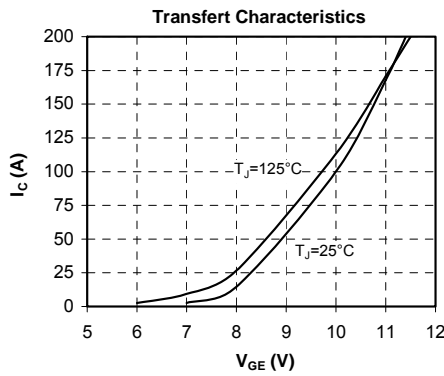
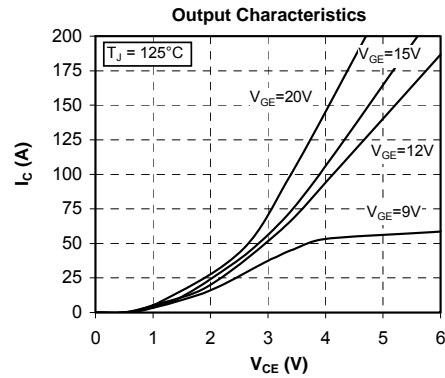
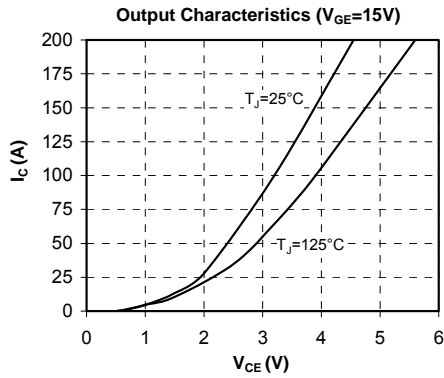
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 100A$		$T_j = 25^\circ C$ 3.2 $T_j = 125^\circ C$ 3.9	3.7	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4mA$	4.5	5.5	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$		6.5		nF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		1		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		0.5		
Q_G	Gate charge	$V_{GE} = \pm 15V; V_{CE} = 600V$ $I_C = 100A$		1.1		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ($25^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 100A$ $R_G = 5.6\Omega$		120		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			310		
T_f	Fall Time			20		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ($125^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 100A$ $R_G = 5.6\Omega$		130		ns
T_r	Rise Time			60		
$T_{d(off)}$	Turn-off Delay Time			360		
T_f	Fall Time			30		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 100A$ $R_G = 5.6\Omega$		$T_j = 125^\circ C$ 12		mJ
E_{off}	Turn-off Switching Energy			$T_j = 125^\circ C$ 5		
I_{sc}	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 900V$ $t_p \leq 10\mu s; T_j = 125^\circ C$		650		A
R_{thJC}	Junction to Case Thermal Resistance				0.19	$^\circ C/W$

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$			250	μA
I_F	DC Forward Current	$T_c = 80^\circ C$		100		A
V_F	Diode Forward Voltage	$I_F = 100A$		2.4	3	V
		$I_F = 150A$		2.7		
		$I_F = 100A$ $T_j = 125^\circ C$		1.8		
t_{rr}	Reverse Recovery Time	$I_F = 100A$ $V_R = 800V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ C$	385		ns
			$T_j = 125^\circ C$	480		
Q_{rr}	Reverse Recovery Charge	$I_F = 100A$ $V_R = 800V$ $di/dt = 200A/\mu s$	$T_j = 25^\circ C$	1055		nC
			$T_j = 125^\circ C$	5240		
R_{thJC}	Junction to Case Thermal Resistance				0.55	$^\circ C/W$



Microsemi reserves the right to change, without notice, the specifications and information contained herein